

MEMORY DEVICE

Abstract of the Disclosure

Embodiments of the present invention provide a magnetic memory. In one embodiment, the magnetic memory comprises an array of memory cells configured to provide resistive states, and a read circuit. The read circuit is configured to sense a resistance through a memory cell in the array of memory cells to obtain a sense result and categorize the sense result into one of at least three different categories comprising a middle category situated between the resistive states.